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**INFORMATION DISCLOSURE
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PTO/USPO/10-011
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 US Patent & Trademark Office U.S. DEPARTMENT OF COMMERCE

Complete if Known

Application Number 10/786,354
 Filing Date February 25, 2004
 First Named Inventor Ahn, Kie
 Group Art Unit 2818
 Examiner Name Huynh, Andy

Attorney Docket No: 303.686US3

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
AK	US-20010002333	05/31/2001	Huang, Chao-Yuan, et al.	438	637	03/29/1999
	US-1,254,987	01/29/1918	Cooper, H. S.			10/15/1917
	US-1,976,375	10/09/1934	Smith, J. K.	148	11.5	01/27/1931
	US20020109233	08/15/2002	Farrar, Paul A.	257	762	04/05/2002
	US-2,244,608	06/03/1941	Cooper, H. S.	75	138	02/09/1939
	US-2,842,438	07/08/1958	Saavivirta, M. J., et al.	75	153	08/02/1956
	US-3,147,110	09/01/1964	Foerster, G. S.	75	122.5	11/27/1961
	US-3,506,438	04/14/1970	Krock, R. H., et al.	75	208	07/24/1967
	US-3,548,948	12/22/1970	Richmond, W. J., et al.	164	68	01/23/1969
	US-3,687,737	08/29/1972	Krock, R. H., et al.	148	2	07/17/1970
	US-3,923,500	12/02/1975	Kitazawa, Kunio, et al.	75	156.5	09/04/1974
	US-4,213,818	07/22/1980	Lemons, Kyle E., et al.	438	719	01/04/1979
	US-5,668,398	09/16/1997	Havemann, R. H., et al.	257	522	04/12/1996
	US-6,197,181	03/06/2001	Chen, Linlin	205	123	03/20/1998
	US-6,268,277	07/31/2001	Bang, D	438	619	07/16/1999
AK	US-6,448,331	09/10/2002	Ioka, T., et al.	524	859	11/12/1999

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AK	EP-0304046	02/22/1989	Fujimura, S., et al.	G03F	7/26	
	JP-05267643	10/15/1993	Muraoka, Toru	029	46	
	JP-07-321111	08/12/1995	Tetsuo, K.	H01L	21/320 5	
AK	JP-07078815	03/20/1995	Miyamoto, I.	H01L	21/320 5	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AK		"Brooks Model 5964 High Performance Metal Seal Mass Flow Controller (Introduced in 1991)", Brooks Instrument, http://www.frco.com/brooks/semiconductor/products11.html , (1991), 1 page	

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Andy Huynh

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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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Application Number	Unknown 10/786,354
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
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	US20020014646	02/07/2002	Tsu, , et al.	257	296	
	US20020028552	03/07/2002	Lee, , et al.	438	243	
	US20020096768	07/25/2002	Joshi, Rajiv Vasant	257	750	
	US-3,337,334	08/22/1967	Fenn, R. W., et al.	75	150	12/06/1963
	US-3,548,915	10/22/1970	Richmond, W. J., et al.	164	68	06/11/1969
	US-3,832,456	08/27/1974	Kobetz, Paul , et al.	423	645	10/18/1962
	US-3,923,500	12/02/1975	Kitazawa, Kunio , et al.	75	156.5	09/04/1974
	US-3,932,226	01/13/1976	Klatskin, J. B., et al.	204	16	12/06/1974
	US-3,954,570	06/04/1976	Shirk, Albert , et al.	204	15	11/11/1974
	US-4,022,931	05/10/1977	Black, J. , et al.	427	91	06/13/1975
	US-4,029,377	06/14/1977	Guglielmi, A. C.	339	19	02/03/1976
	US-4,065,330	12/27/1977	Masumoto, Hakanu , et al.	148	31.55	02/22/1977
	US-4,101,855	07/18/1978	Drapeau, Donald R.	335	106	11/05/1976
	US-4,158,719	06/19/1979	Frantz, E.	428	567	06/09/1977
	US-4,233,066	11/11/1980	Sundin, Anders O., et al.	75	142	08/14/1975
	US-4,314,594	02/09/1982	Pfeifer, Friedrich , et al.	148	108	04/29/1980
	US-4,386,116	05/31/1983	Nair, Krishna K., et al.	427	99	12/24/1981
	US-4,389,429	06/21/1983	Soclof, Sidney I.	438	492	06/28/1982
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	US-4,423,547	01/03/1984	Farrar, P. A., et al.	29	571	06/01/1981
	US-4,561,173	12/31/1985	Te Velde, T. S.	438	619	06/07/1983
	US-4,565,157	01/21/1986	Brors, D. L., et al.	118	719	03/29/1983
	US-4,574,095	03/04/1986	Baum, Thomas H., et al.	427	53.1	11/19/1984
	US-4,670,297	06/02/1987	Lee, K. , et al.	427	91	06/21/1985
	US-4,709,359	11/24/1987	Loftin, Rayford A.	367	155	06/28/1982
	US-4,762,728	08/09/1988	Keyser, T. , et al.	427	38	11/26/1985
	US-4,788,082	11/29/1988	Schmitt, Jerome J.	427	248.1	12/12/1985
	US-4,847,111	07/11/1989	Chow, Yu C., et al.	427	38	06/30/1988
	US-4,857,481	08/15/1989	Tam, G. , et al.	437	182	03/14/1989
al	US-4,931,410	06/05/1990	Tokunaga, Takafumi , et al.	437	189	08/25/1988

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.686US3

ah	US-4,948,459	08/14/1990	Van Laarhoven, , et al.	156	643	01/04/1989
	US-4,962,058	10/09/1990	Cronin, John E., et al.	437	187	04/14/1989
	US-4,996,584	02/26/1991	Young, P. L., et al.	357	71	10/13/1988
	US-5,019,531	05/28/1991	Awaya, N., et al.	437	180	05/19/1989
	US-5,034,799	07/23/1991	Tomita, K., et al.	357	71	02/14/1990
	US-5,045,635	09/02/1991	Kaplo, Joseph J., et al.	174	35 GC	06/16/1989
	US-5,084,412	01/28/1992	Nakasaki, Yasushi	437	189	10/01/1990
	US-5,100,499	03/31/1992	Douglas, M. A.	156	635	06/25/1991
	US-5,130,274	07/14/1992	Harper, J. M., et al.	437	195	04/05/1991
	US-5,148,260	09/15/1992	Inoue, T., et al.	357	67	09/07/1990
	US-5,149,615	09/22/1992	Chakravorty, K. K., et al.	430	313	01/08/1991
	US-5,158,986	10/27/1992	Cha, S. W., et al.	521	82	04/05/1991
	US-5,173,442	12/22/1992	Carey, D. H.	437	173	03/24/1992
	US-5,227,658	07/13/1993	Beyer, K., et al.	257	522	10/23/1991
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	US-5,232,866	08/03/1993	Beyer, K., et al.	437	62	10/23/1991
	US-5,240,878	08/31/1993	Fitzsimmons, J., et al.	437	187	04/26/1991
	US-5,243,222	09/07/1993	Harper, J. M., et al.	257	774	01/08/1992
	US-5,256,205	10/26/1993	Schmitt III, Jerome J., et al.	118	723	01/07/1992
	US-5,268,315	12/07/1993	Prasad, J. S., et al.	437	31	09/04/1992
	US-5,308,440	05/03/1994	Chino, T., et al.	156	664	09/02/1992
	US-5,324,683	06/28/1994	Fitch, J. T., et al.	437	65	06/02/1993
	US-5,324,684	06/28/1994	Kermani, Ahmad, et al.	437	95	02/25/1992
	US-5,334,356	08/02/1994	Baldwin, D. F., et al.	422	133	08/24/1992
	US-5,336,914	08/09/1994	Andoh, Takeshi	257	368	08/19/1992
	US-5,354,712	10/11/1994	Ho, Y. Q., et al.	437	195	11/12/1992
	US-5,356,672	10/18/1994	Schmitt III, J. J., et al.	427	446	05/09/1990
	US-5,371,042	12/06/1994	Ong, E.	437	184	06/16/1992
	US-5,384,284	01/24/1995	Doan, T T., et al.	437	190	10/01/1993
	US-5,399,897	03/21/1995	Cunningham, B. T., et al.	257	467	11/29/1993
	US-5,408,742	04/25/1995	Zaidel, S. A., et al.	29	846	10/22/1993
	US-5,413,687	05/09/1995	Barton, C. L., et al.	204	192.14	11/27/1991
	US-5,413,962	05/09/1995	Lur, Water, et al.	437	195	07/15/1994
	US-5,424,030	06/13/1995	Takahashi, H.	420	473	12/03/1993
ah	US-5,426,330	06/20/1995	Joshi, R. V., et al.	257	752	09/21/1993

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.686US3

ah	US-5,442,237	08/15/1995	Hughes, Henry G., et al.	257	759	02/04/1994
	US-5,444,015	08/22/1995	Aitken, John M., et al.	437	182	04/11/1994
	US-5,447,887	09/05/1995	Filipiak, Stanley, et al.	437	200	04/01/1994
	US-5,457,344	10/10/1995	Bartelink, Dirk J.	257	737	03/25/1994
	US-5,470,789	11/28/1995	Misawa, N.	437	190	03/07/1995
	US-5,470,801	11/28/1995	Kapoor, Ashok K., et al.	437	238	06/28/1993
	US-5,476,817	12/19/1995	Numata, K.	437	195	05/31/1994
	US-5,485,037	01/16/1996	Marrs, R. C.	257	712	03/27/1995
	US-5,495,667	03/05/1996	Farnworth, Warren M., et al.	29	843	11/07/1994
	US-5,506,449	04/09/1996	Nakano, Tadashi, et al.	257	758	03/23/1994
	US-5,510,645	04/23/1996	Fitch, J. T., et al.	257	522	01/17/1995
	US-5,529,956	06/25/1996	Morishita, Y.	437	195	09/28/1994
	US-5,534,731	07/09/1996	Cheung, Robin	257	759	10/28/1994
	US-5,538,922	07/23/1996	Cooper, K J., et al.	437	195	01/25/1995
	US-5,539,060	07/23/1996	Tsunogae, Y., et al.	525	338	10/13/1995
	US-5,539,227	07/23/1996	Nakano, H.	257	276	08/02/1995
	US-5,578,146	11/26/1996	Grant, L. A., et al.	148	437	01/16/1996
	US-5,595,937	01/21/1997	Mikagi, K.	437	192	04/12/1996
	US-5,609,721	03/11/1997	Tsukune, A., et al.	156	646.1	01/03/1995
	US-5,625,232	04/29/1997	Numata, K., et al.	257	758	07/15/1994
	US-5,635,253	06/03/1997	Canaperi, Donald F., et al.	427	437	06/07/1995
	US-5,654,245	08/05/1997	Allen, Gregory L.	438	629	03/23/1993
	US-5,662,788	09/02/1997	Sandhu, G., et al.	205	87	06/03/1996
	US-5,667,600	09/18/1997	Grensing, Fritz C., et al.	148	437	03/31/1994
	US-5,670,420	09/23/1997	Choi, Kyeong K.	437	189	11/08/1995
	US-5,674,787	10/07/1997	Zhao, Bin, et al.	437	230	01/16/1996
	US-5,675,187	10/07/1997	Numata, K., et al.	257	758	05/16/1996
	US-5,679,608	10/21/1997	Cheung, Robin W., et al.	437	195	06/05/1995
	US-5,681,441	10/28/1997	Svendsen, Leo G., et al.	205	114	12/22/1992
	US-5,695,810	12/09/1997	Dubin, Valery M., et al.	427	96	11/20/1996
	US-5,705,425	01/06/1998	Miura, T., et al.	437	182	04/26/1996
	US-5,719,089	02/17/1998	Cherng, Meng-Jaw, et al.	438	637	06/21/1996
ah	US-5,719,410	02/17/1998	Suehiro, S., et al.	257	77	12/16/1996

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.686US3

AL	US-5,725,689	03/10/1998	Nishida, S., et al.	148	320	10/05/1995
	US-5,739,579	04/14/1998	Chiang, Chien, et al.	257	635	09/10/1996
	US-5,763,953	06/09/1998	Iijima, T., et al.	257	762	01/18/1996
	US-5,780,358	07/14/1998	Zhou, M. S.	438	645	04/08/1996
	US-5,785,570	07/28/1998	Bruni, M. D.	445	52	07/25/1995
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	US-5,792,706	08/11/1998	Michael, M. W., et al.	438	626	06/05/1996
	US-5,801,098	09/01/1998	Fiordalice, R., et al.	438	653	09/03/1996
	US-5,814,557	09/29/1998	Venkatraman, Ramnath, et al.	438	622	05/20/1996
	US-5,821,168	10/13/1998	Jain, Ajay	438	692	07/16/1997
	US-5,824,599	10/20/1998	Schacham-Diamond, Yosef, et al.	438	678	01/16/1996
	US-5,852,871	12/29/1998	Khandros, I. Y.	29	843	12/11/1995
	US-5,858,877	01/12/1999	Dennison, C. H., et al.	438	700	01/21/1997
	US-5,880,018	03/01/1999	Boeck, Bruce A., et al.	438	619	
✓	US-5,891,797	04/06/1998	Farrar, P. A.	438	619	10/20/1997
	US-5,891,804	04/06/1999	Havemann, R. H., et al.	438	674	04/14/1997
	US-5,893,752	04/13/1999	Zhang, J., et al.	438	687	12/22/1997
	US-5,895,740	04/20/1999	Chien, Rong-Wu, et al.	430	313	11/13/1996
	US-5,897,370	04/27/1999	Joshi, R. V., et al.	438	632	10/28/1996
	US-5,900,668	05/04/1999	Wollesen, D. L.	257	522	11/30/1995
	US-5,907,772	05/25/1999	Iwasaki, Haruo	438	253	02/26/1997
	US-5,911,113	06/08/1999	Yao, G., et al.	438	649	03/18/1997
	US-5,913,147	06/15/1999	Dubin, Valery, et al.	438	687	01/21/1997
	US-5,925,930	07/20/1999	Farnworth, Warren M., et al.	257	737	05/21/1996
	US-5,930,596	07/27/1999	Klose, H., et al.	438	98	03/07/1995
	US-5,930,669	07/27/1999	Uzoh, Cyprian	438	627	04/03/1997
	US-5,932,928	08/03/1999	Clampitt, D. A.	257	758	07/03/1997
	US-5,933,758	08/03/1999	Jain, A.	438	687	05/12/1997
	US-5,940,733	08/17/1999	Beinglass, Israel, et al.	438	655	07/29/1997
	US-5,948,467	09/07/1999	Nguyen, T., et al.	427	99	07/24/1998
	US-5,962,923	10/05/1999	Xu, Z., et al.	257	774	08/07/1995
	US-5,968,333	10/19/1999	Nogami, T., et al.	205	184	04/07/1998
	US-5,969,422	10/19/1999	Ting, C., et al.	257	762	05/15/1997
	US-5,972,179	10/26/1999	Chittipeddi, et al.	204	192.17	09/30/1997
AL	US-5,972,804	10/26/1999	Tobin, Philip J., et al.	438	786	11/03/1997
	US-5,976,710	11/02/1999	Sachdev, K. G., et al.	428	620	04/10/1997

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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.686US3

ah	US-5,981,350	11/09/1999	Geusic, Joseph E., et al.	438	386	05/29/1998
	US-5,985,759	11/16/1999	Kim, E., et al.	438	653	02/24/1998
	US-5,989,623	11/23/1999	Chen, Liang-Yuh, et al.	427	97	08/19/1997
	US-5,994,776	11/30/1999	Fang, Peng, et al.	257	758	04/20/1998
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	US-6,001,730	12/14/1999	Farkas, J., et al.	438	627	10/20/1997
	US-6,004,884	12/21/1999	Abraham, L. C.	438	714	02/15/1996
	US-6,008,117	12/28/1999	Hong, Qi-Zhong, et al.	438	629	03/19/1997
	US-6,015,465	01/18/2000	Kholodenko, A., et al.	118	719	04/08/1998
	US-6,015,738	01/18/2000	Levy, H. J., et al.	438	275	11/17/1997
	US-6,017,820	01/25/2000	Ting, C. H., et al.	438	689	07/17/1998
	US-6,022,802	02/08/2000	Jang, Syun-Ming	438	656	03/18/1999
	US-6,025,261	02/15/2000	Farrar, C., et al.	438	619	04/29/1998
	US-6,030,877	02/29/2000	Lee, C, et al.	438	381	10/06/1997
	US-6,037,248	03/14/2000	Ahn, Kie	438	619	06/13/1997
	US-6,054,172	04/25/2000	Robinson, K., et al.	427	97	02/25/1999
	US-6,057,226	05/02/2000	Wong, L. D.	438	623	11/25/1997
	US-6,065,424	05/23/2000	Shacham-Diamand, Y., et al.	118	696	12/18/1996
	US-6,069,068	05/30/2000	Rathore, H. S., et al.	438	628	10/08/1997
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Group Art Unit	Unknown
Examiner Name	Unknown

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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Application Number	Unknown
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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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